

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

BXL4004 — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)1=3m Ω (typ.)
- Input capacitance Ciss=8200pF (typ.)

• 4.5V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

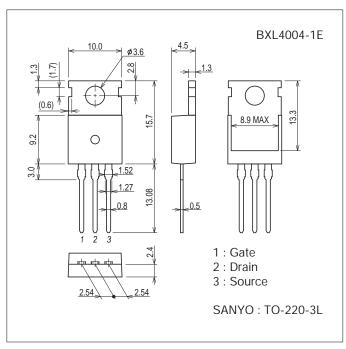
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		40	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	ID		100	Α
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	400	Α
Allowable Power Dissipation	D-		1.75	W
	PD	Tc=25°C	75	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		420	mJ
Avalanche Current *2	I _{AV}		60	Α

Note :*1 V_{DD} =24V, L=100 μ H, I_{AV} =60A (Fig.1)

*2 L≤100µH, Single pulse

Package Dimensions

unit : mm (typ) 7536-001

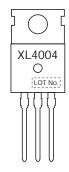


Product & Package Information

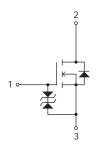
• Package : TO-220-3L

• JEITA, JEDEC : SC-46, TO-220AB • Minimum Packing Quantity : 50 pcs./magazine

Marking



Electrical Connection

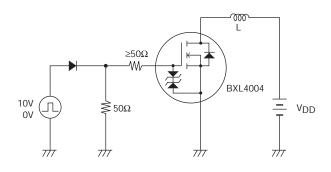


Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions		Unit			
Parameter	Syllibol	Conditions	min	typ	max		
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	40			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =40V, V _{GS} =0V			10	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V	
Forward Transfer Admittance	yfs	VDS=10V, ID=50A		120		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	ID=50A, VGS=10V		3	3.9	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	ID=50A, VGS=4.5V		4.7	6.6	mΩ	
Input Capacitance	Ciss			8200		pF	
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		940		pF	
Reverse Transfer Capacitance	Crss			700		pF	
Turn-ON Delay Time	t _d (on)			65		ns	
Rise Time	t _r	See Fig.2		390		ns	
Turn-OFF Delay Time	t _d (off)			510		ns	
Fall Time	tf			360		ns	
Total Gate Charge	Qg			140		nC	
Gate-to-Source Charge	Qgs	V _{DS} =24V, V _{GS} =10V, I _D =100A		43		nC	
Gate-to-Drain "Miller" Charge	Qgd			25		nC	
Diode Forward Voltage	VSD	IS=100A, VGS=0V		1.0	1.2	V	
Reverse Recovery Time	t _{rr}	See Fig.3		90		ns	
Reverse Recovery Charge	Q _{rr}	IS=100A, VGS=0V, di/dt=100A/μs		230		nC	

Fig.1 Unclamped Inductive Switching Test Circuit

Fig.2 Switching Time Test Circuit



V_{IN} V_{DD=24V}

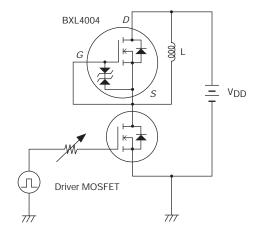
10V V_{IN} I_{D=50A}

V_{IN} R_{L=0.48Ω}

PW=10μs
D.C.≤1%

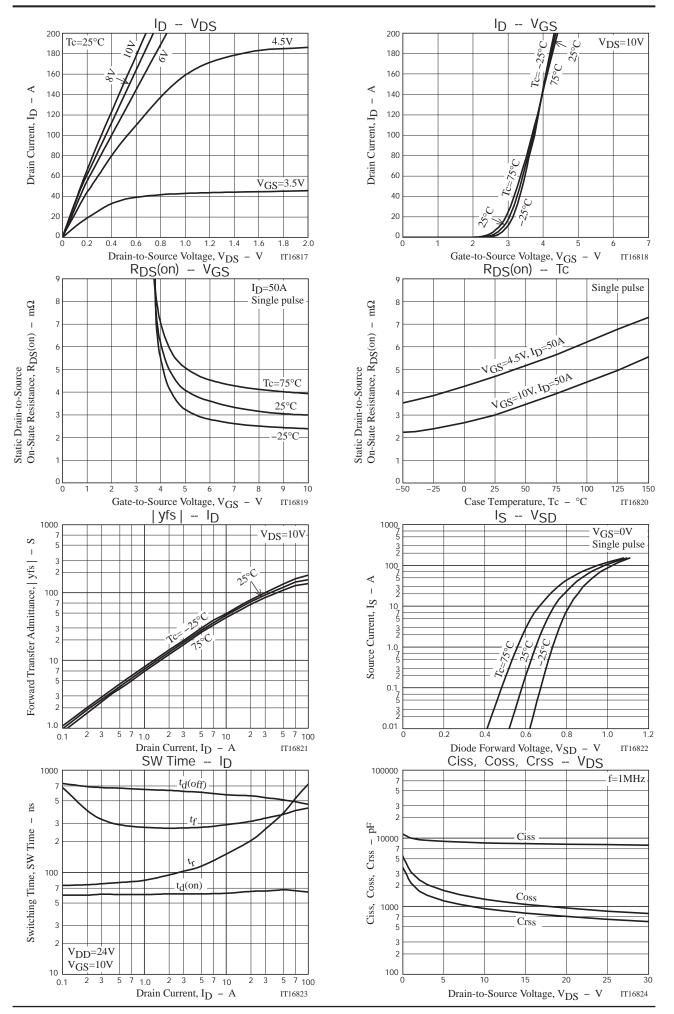
BXL4004

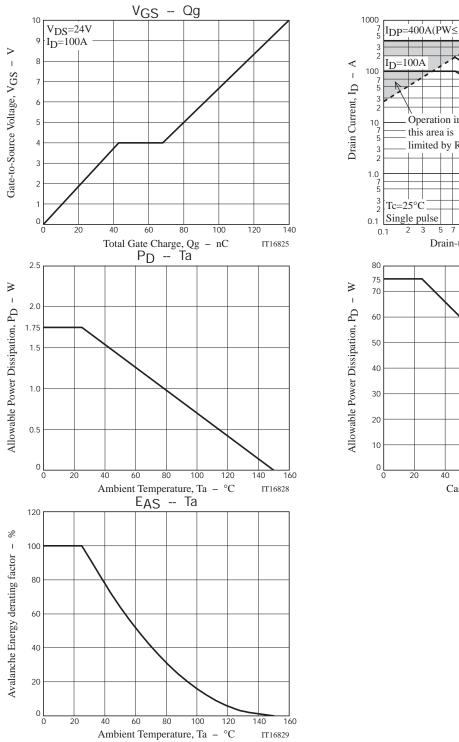
Fig.3 Reverse Recovery Time Test Circuit

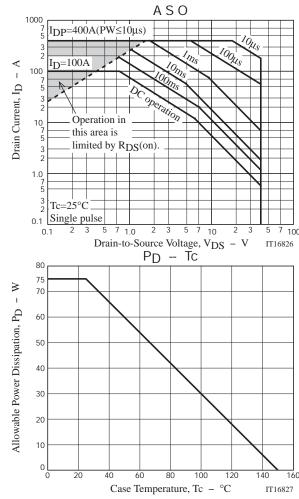


Ordering Information

Device	Package	Shipping	memo	
BXL4004-1E	TO-220-3L	50pcs./magazine	Pb Free and Halogen Free	







Magazine Specification

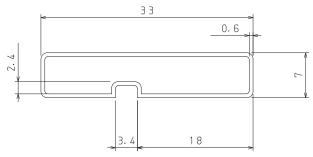
BXL4004-1E

1. Packing Format

Package Name	Maximum Number of devices contained (pcs)			Packing	format
1 4 0 14 8 0 14 4 110	Magazine	Inner box	Outer box	Inner BOX	Outer BOX
TO-220-3L	50	1,000	4000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPD-LV0010 4 inner boxes contained Dimensions:mm (external) 590x225x178

2. Magazine dimensions

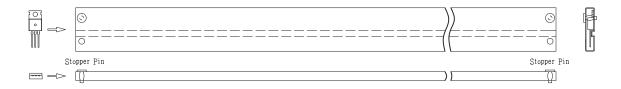
(unit:mm)



To lerance= ± 0 . 2mm Thickness=0. 6+0. 2/-0mm Length =512. 6 ± 1 mm

Material = PVC (Antistatic treatment)

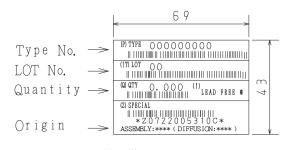
3. Storage method to magazine

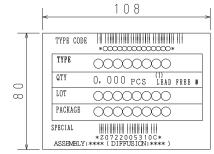


4. Inner box label (unit:mm)

5. Outer box label (unit:mm)

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



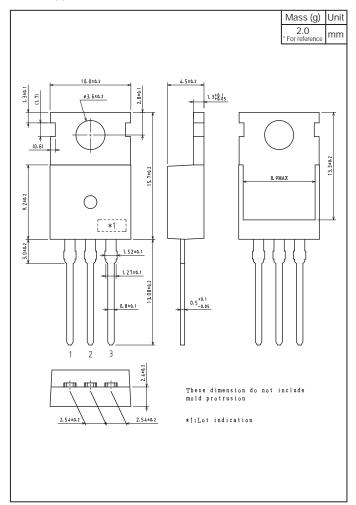


The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase
LEAD FREE	3	JEITA Phase 3A

Outline Drawing

BXL4004-1E



Note on usage: Since the BXL4004 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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